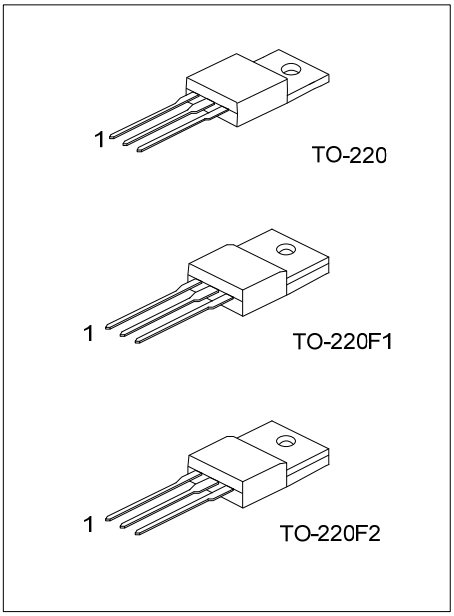
40A, 150V N-CHANNEL POWER MOSFET



■ DESCRIPTION

The UTC **40N15** is a N-channel enhancement MOSFET, it uses UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

■ FEATURES

* $R_{DS(ON)}$ < 50mΩ @ V_{GS}=10V, I_D=20A
* High Switching Speed
* High Current Capacity

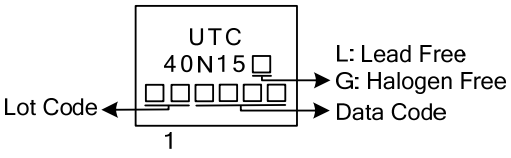
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
40N15L-TA3-T	40N15G-TA3-T	TO-220	G	D	S	Tube
40N15L-TF1-T	40N15G-TF1-T	TO-220F1	G	D	S	Tube
40N15L-TF2-T	40N15G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

40N15G-TA3-T (1)Packing Type (2)Package Type (3)Green Package	(1) T: Tube (2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	150	V
Gate-Source Voltage		V_{GSS}	±25	V
Drain Current	Continuous	I_D	40	A
	Pulsed	I_{DM}	180	A
Avalanche Current		I_{AR}	45.6	A
Avalanche Energy	Single Pulsed	E_{AS}	650	mJ
	Repetitive	E_{AR}	21	mJ
Peak Diode Recovery dv/dt		dv/dt	7	V/ns
Power Dissipation	TO-220	P_D	166	W
	TO-220F1/TO-220F2		40	W
Junction Temperature		T_J	-50 ~ +150	°C
Storage Temperature Range		T_{STG}	-50 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-220	θ_{JC}	0.9	°C/W
	TO-220F1/TO-220F2		3.125	°C/W

■ ELECTRICAL CHARACTERISTICS

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	150			V
Drain-Source Leakage Current		I_{DSS}	V_{GS}=0V, V_{DS}=150V			900	nA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+20V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-20V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.2		3.8	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=20A			50	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz		2500		pF
Output Capacitance		C_{OSS}			520		pF
Reverse Transfer Capacitance		C_{RSS}			100		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{GS}=10V, V_{DD}=50V, I_D=1.3A, I_G=100μA		85		nC
Gate to Source Charge		Q_{GS}			15		nC
Gate to Drain Charge		Q_{GD}			41		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{GS}=0~10V, V_{DD}=30V, I_D=0.5A, R_G=25Ω		35		ns
Rise Time		t_R			320		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			210		ns
Fall-Time		t_F			200		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				40	A
Maximum Body-Diode Pulsed Current		I_{SM}				160	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=40A, V_{GS}=0V			1.48	V
Body Diode Reverse Recovery Time		t_{RR}	V_{GS}=0V, I_S=30A, dI_F/d_t=100A/μs		150		ns
Body Diode Reverse Recovery Charge		Q_{RR}			0.9		μC

■ TYPICAL CHARACTERISTICS